

/ Descriptions

Silicon PNP transistor in a TO-220F Plastic Package.

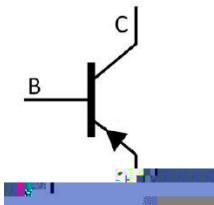
/ Features

High f_T , complementary pair with 2SC5171.

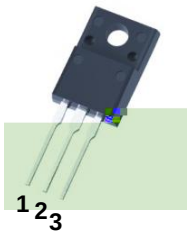
/ Applications

General power and driver stage amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-180	V
Collector to Emitter Voltage	V_{CEO}	-180	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-2.0	A
Base Current	I_B	-1.0	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	$P_C(T_c=25^\circ C)$	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

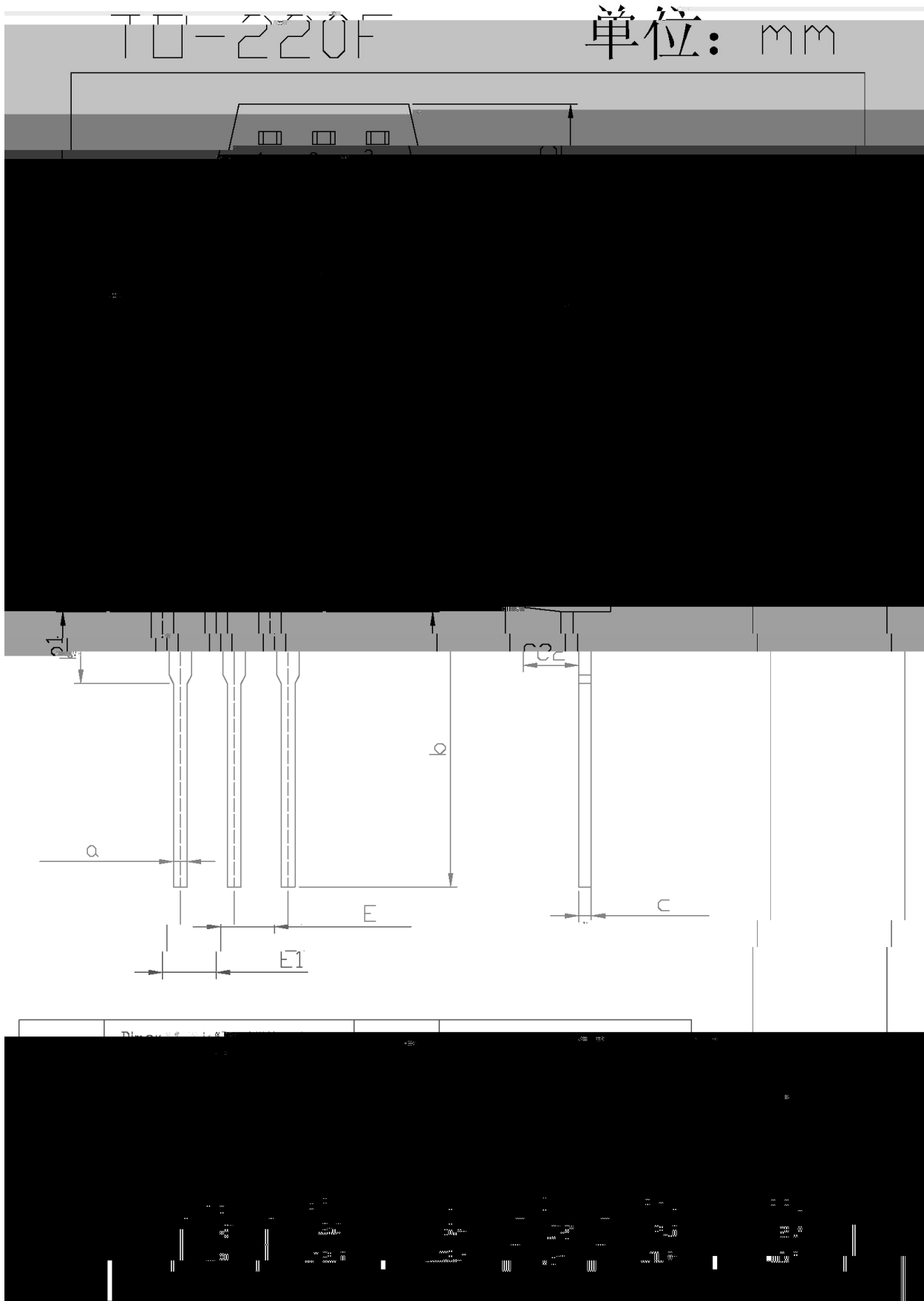
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	V_{CEO}	$I_C=-10mA$ $I_B=0$	-180			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-180V$ $I_E=0$			-5.0	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-5.0	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-5.0V$ $I_C=-100mA$	100		320	
	$h_{FE(2)}$	$V_{CE}=-5.0V$ $I_C=-1.0A$	50			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-1.0A$ $I_B=-100mA$			0.310.0054	Tc01

18.

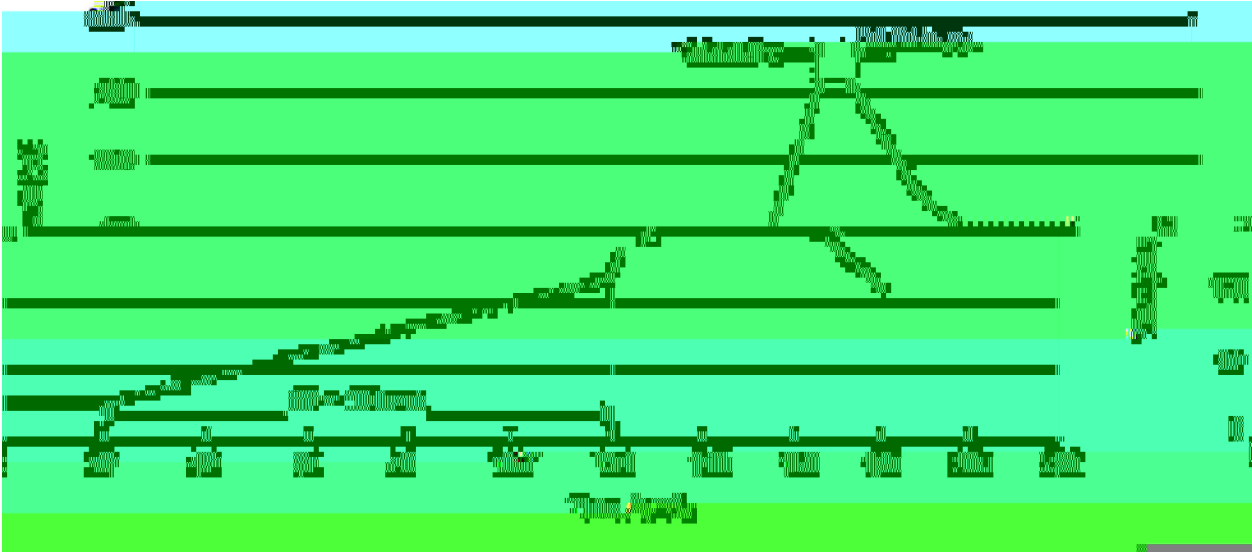
/ Electrical Characteristic Curve



/ Package Dimensions



() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-----|-----|----|---------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255 | 5 | 5 | 0.5sec; | 2.Peak Temp.:255 5 , Duration:5 0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

5	255
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